# 8k, 16k bit EEPROMs for direct connection to serial ports

# BR9080 / BR9080F / BR9080RFV / BR9016 / BR9016F / BR9016RFV

The BR9080 and BR9016 series are serial EEPROMs that can be connected directly to a serial port and can be erased and written electrically. Writing and reading is performed in word units, using four types of operation commands. Communication occurs though  $\overline{CS}$ ,  $\overline{SK}$ , DI, and DO pins,  $\overline{WC}$  pin control is used to initiate a write disabled state, enabling these EEPROMs to be used as one-time ROMs. During writing, operation is checked via the internal status check.

#### Applications

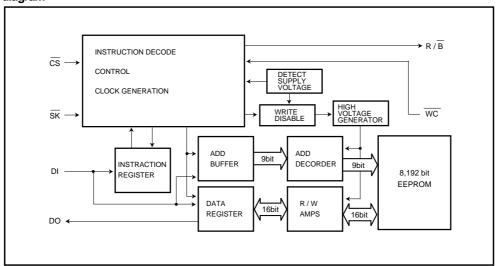
Movie, camera, cordless telephones, car stereos, VCRs, TVs, DIP switches, and other battery-powered equipment requiring low voltage and low current

#### Features

- 1) BR9080 / F / RFV (8k bit): 512 words  $\times$ 16 bits BR9016 / F / RFV (16k bit): 1024 words  $\times$  16bits
- 2) Single power supply operation
- 3) Serial data input and output
- 4) Automatic erase-before-write
- 5) Low current consumption Active (5V) : 5mA (max.) Standby (5V) : 3µA (max.)

- 6) Noise filter built into SK pin
- 7) Write protection when Vcc is low
- 8) Compact DIP8 / SOP8 / SSOP-B8 packages
- 9) High reliability CMOS process
- 10) 100,000 ERASE / WRITE cycles
- 11) 10 years Data Retention

#### Block diagram



# Pin descriptions

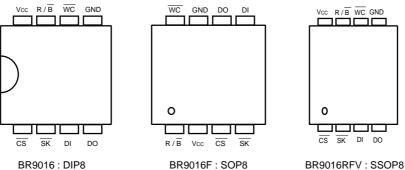


Fig.1

Pin No.		Pin name	Function		
DIP / SSOP	SOP	Pinname	Function		
1	3	CS	Chip Select Control		
2	4	SK	Serial Data Clock Input		
3	5	DI	Op code, address, Serial Data Input		
4	6	DO	Serial Data Output		
5	7	GND	Ground 0V		
6	8	WC	Write Control Input		
7	1	R/B	READY / BUSY Output		
8	2	Vcc	Power supply		

# ● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Lim	Unit	
Supply voltage	Vcc	-0.3~+7.0		V
		DIP8	500*1	
Power dissipation	Pd	SOP8	350*2	mW
		SSOP-B8	300*3	
Storage temperature	Tstg	-65~+125		°C
Operation temperature	Topr	-40-	°C	
Input voltage	-	-0.3~V	-0.3~Vcc+0.3	

# ● Recommended operating conditions (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	
Power supply voltage	WRITE	Vcc	2.7	_	5.5	V
	READ	VCC	2.7	_	5.5	V
Input voltage	Vin	0	_	Vcc	V	

<sup>\*1</sup> Reduced by 5.0mW for each increase in Ta of 1°C over 25°C.
\*2 Reduced by 3.5mW for each increase in Ta of 1°C over 25°C.
\*3 Reduced by 3.0mW for each increase in Ta of 1°C over 25°C.

# •Electrical characteristics

BR9080 / F / RFV, BR9016 / F / RFV: 5V (Unless otherwise noted, Ta=-40~85°C, Vcc=2.7V~5.5V)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Input low level voltage 1	VIL1	-	-	0.3×Vcc	V	DI pin
Input high level voltage 1	V <sub>IH1</sub>	0.7×Vcc	-	_	V	DI pin
Input low level voltage 2	VIL2	_	-	0.2×Vcc	٧	CS, SK, WC pin
Input high level voltage 2	V <sub>IH2</sub>	0.8×Vcc	-	_	V	CS, SK, WC pin
Output low level voltage	Vol	0	-	0.4	V	loL=2.1mA
Output high level voltage	Vон	Vcc-0.4	-	Vcc	V	IoH=-0.4mA
Input leak current	lц	-1	-	1	μΑ	Vin=0V~Vcc
Output leak current	ILO	-1	-	1	μΑ	Vout=0V~Vcc, CS=Vcc
Consumption current	Icc1	_	-	5	mA	fsκ=2MHz tE / W=10ms (WRITE)
during operation	Icc2	_	-	3	mA	fsκ=2MHz (READ)
Standby current	IsB	_	-	3	μΑ	CS / SK / DI / WC=Vcc DO, R / B=OPEN
SK frequency	fsк	_	_	2	MHz	-

# $BR9080 \, / \, F \, / \, RFV, \, BR9016 \, / \, F \, / \, RFV \! : \, 3V \, (Unless \, otherwise \, noted, \, Ta = -40 - 85^{\circ}C, \, Vcc = 2.7V - 5.5V)$

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Input low level voltage 1	VIL1	-	-	0.3×Vcc	V	DI pin
Input high level voltage 1	V <sub>IH1</sub>	0.7×Vcc	-	-	V	DI pin
Input low level voltage 2	VIL2	_	-	0.2×Vcc	V	CS, SK, WC pin
Input high level voltage 2	V <sub>IH2</sub>	0.8×Vcc	-	-	V	CS, SK, WC pin
Output low level voltage	Vol	0	-	0.4	V	IoL=100μA
Output high level voltage	Vон	Vcc-0.4	-	Vcc	V	Іон=-100μА
Input leak current	lu	-1	-	1	μΑ	Vin=0V~Vcc
Output leak current	ILO	-1	-	1	μΑ	Vout=0V~Vcc, CS=Vcc
Consumption current	Icc1	-	-	3	mA	fsk=2MHz tE / W=10ms (WRITE)
during operation	Icc2	_	-	750	μΑ	fsk=2MHz (READ)
Standby current	IsB	_	-	2	μΑ	CS/SK/DI/WC=Vcc DO, R/B=OPEN
SK frequency	fsк	-	-	2	MHz	-

Not designed for radiation resistance

# Operating timing characteristics

BR9080/F/RFV, BR9016/F/RFV (Unless otherwise noted, Ta=-40~85°C, Vcc=2.7V~5.5V)

Parameter	Symbol	Min.	Тур.	Max.	Unit
CS setup time	fcss	100	-	-	ns
CS hold time	<b>t</b> csH	100	_	_	ns
Data setup time	tois	100	-	-	ns
Data hold time	tын	100	-	-	ns
DO rise delay time	<b>t</b> PD1	-	-	150	ns
DO fall delay time	t <sub>PD0</sub>	-	-	150	ns
Self-timing programming cycle	te/w	-	-	10	ms
CS minimum high level time	tcs	250	-	-	ns
READY / BUSY display valid time	tsv	ı	-	150	ns
Time when DO goes HIGH-Z (via $\overline{\text{CS}}$ )	tон	0	_	150	ns
Data clock high level time	twн	250	-	-	ns
Data clock low level time	tw∟	250	-	-	ns
Write control setup time	twcs	0	-	-	ns
Write control hold time	twcн	0	_	_	ms

#### Timing chart

Synchronous Data Input Output Timing

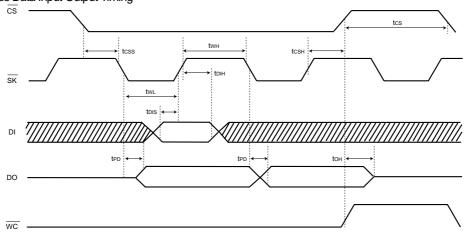


Fig.2

- Input data are clocked in to DI at the rising edge of the clock  $(\overline{\text{SK}}).$
- $\cdot$  Output data will toggle on the falling edge of the  $\overline{\text{SK}}$  clock.
- $\cdot$  The  $\overline{\text{WC}}$  pin does not have any effect on the READ, EWEN and EWDS operations.

# Circuit operation

# (1) Command mode

#### BR9080

Instruction	Start Bit	Op Code	Address	Data
Read (READ)	1010	100 A0	A1 A2 A3 A4 A5 A6 A7 A8	
Write (WRITE)	1010	010 A0	A1 A2 A3 A4 A5 A6 A7 A8	D0 D1 – D14 D15
Erase / Write enable (EWEN)	1010	0011	* * * * * * * *	
Erase / Write disable (EWDS)	1010	0000	* * * * * * * *	

<sup>\*:</sup> Means either VIH or VIL

#### BR9016

Instruction	Start Bit	Op Code	Address	Data
Read (READ)	1010	10 A0 A1	A2 A3 A4 A5 A6 A7 A8 A9	
Write (WRITE)	1010	01 A0 A1	A2 A3 A4 A5 A6 A7 A8 A9	D0 D1 – D14 D15
Erase / Write enable (EWEN)	1010	0011	* * * * * * * *	
Erase / Write disable (EWDS)	1010	0000	* * * * * * * *	

<sup>\*:</sup> Means either VIH or VIL

# (2) Writing enabled / disabled

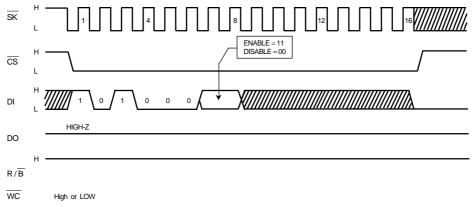


Fig.3

- 1) When  $\overline{\text{CS}}$  is "HIGH" during power up, BR9080 / F / RFV, BR9016 / F / RFV comes up in the erase / write disabled (EWDS) state. In order to be programmable, it must receive an enable (EWEN) instruction.
  - The device remains programmable until a disable (EWDS) instruction is entered, or until it is powered down.
- 2) It is unnecessary to add the clock after 16th clock.

Address and data are transferred from LSB.

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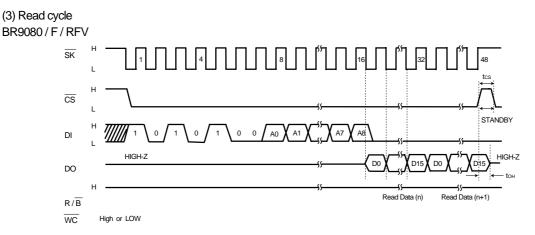


Fig.4 BR9080 / F / RFV

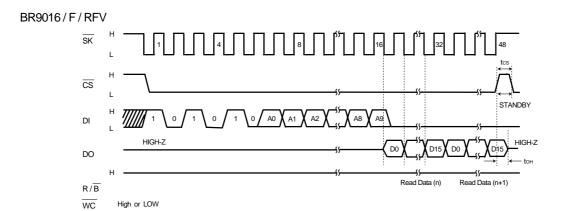


Fig.5 BR9016 / F / RFV

- 1) After the fall of the 16th clock pulse, 16-bit data is output from the DO pin in synchronization with the falling edge of the SK signal.
  - (DO output changes at a time lag of tpd0, tpd1 because of internal circuit delay following the falling edge of the SK signal. During the tpd and tpd1 timing, the tpd time should be assured before data is read, to avoid the previous data being lost. See the synchronized data input / output timing chart in Fig.2.)

2)

# (4) Write cycle BR9080 / F / RFV

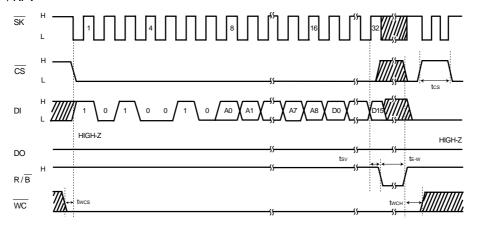


Fig.6 BR9080 / F / RFV

#### BR9016/F/RFV

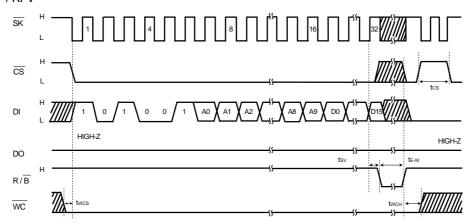


Fig.7 BR9016 / F / RFV

- 1) At the rising edge of 32nd clock,  $R/\overline{B}$  pin will be come out "LOW" after the specified time delay (tsv).
- 2) From above edge R /  $\overline{B}$  will indicate the ready / busy status of the chip: "LOW" indicated programming is all in progress: "HIGH" indicates the write cycle is complete and this part is ready for another instruction.
- 3) During the input of Write command,  $\overline{\text{CS}}$  must be "LOW". However, once the write operation started,  $\overline{\text{CS}}$  could be either "HIGH" or "LOW".
- 4) If WC becomes "HIGH" during Write Cycle, the write operation is halted. In this case, the address data in writing is no guaranteed. It is necessary to rewrite it.

- (5) READY / BUSY display (R / B pin and DO pin: BR9080 / F / RFV, BR9016 / F / RFV)
- 1) This display outputs the internal status signal; the R /  $\overline{B}$  pin outputs the HIGH or LOW status at all times. The display can also be output from the DO pin. Following completion of the writing command, if  $\overline{CS}$  falls while  $\overline{SK}$  is LOW, either HIGH or LOW is output. (The display can also be output without using the R /  $\overline{B}$  pin, leaving it open.)
- 2) When writing data to a memory cell, the READY /  $\overline{BUSY}$  display is output from the rise of the 32nd clock pulse of the  $\overline{SK}$  signal after tsv, from the R /  $\overline{B}$  pin.
  - $R/\overline{B}$  display = LOW: writing in progress

(The internal timer circuit is activated, and after the te/w timing has been created, the timer circuit stops automatically. Writing of data to the memory cell is done during the te/w timing, during which time other commands cannot be received.)

 $R/\overline{B}$  display = HIGH: command standby state

(Writing of data to the memory cell has been completed and the next command can be received.)

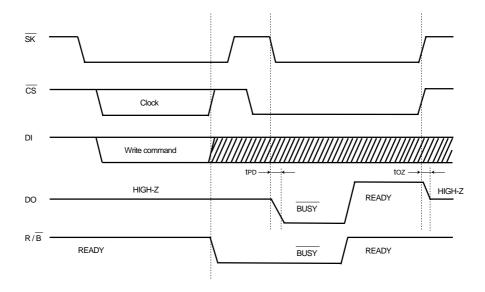


Fig.8 R / B Status Output timing chart

1) D0 will output R /  $\overline{B}$  status after  $\overline{CS}$  is held low during  $\overline{SK}$ =L, until  $\overline{CS}$  is held high.

Note: The document may be strategic technical data subject to COCOM regulations.

#### Operation notes

- (1) Turning the power supply on and off
- 1) When the power supply is turned on and off,  $\overline{\text{CS}}$  should be set to HIGH (=Vcc).
- 2) When  $\overline{\text{CS}}$  is LOW, the command input reception state (active) is entered. If the power supply is turned on in this state, erroneous operations and erroneous writing can occur because of noise and other factors. To avoid this, make sure  $\overline{\text{CS}}$  is set to HIGH (=Vcc) before turning on the power supply.

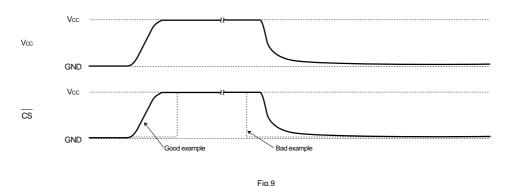
(Good example) Here, the  $\overline{\text{CS}}$  pin is pulled up to Vcc.

When turning off the power supply, wait at least 10msec before turning it on again. Failing to observe this condition can result in the internal circuit failing to be reset when the power supply is turned on.

(Bad example)  $\overline{CS}$  is LOW when the power supply is turned on or off.

In this case, because  $\overline{\text{CS}}$  remains LOW, the EEPROM may perform erroneous operations or write erroneous data because of noise or other factors.

\* Please be aware that the case shown in this example can also occur if  $\overline{\text{CS}}$  input is HIGH-Z.



#### (2) Noise countermeasures

1) SK noise

If noise occurs at the rise of the  $\overline{\text{SK}}$  clock input, the clock is assumed to be excessive, and this can cause malfunction because the bits are out of alignment.

2) WC noise

During a writing operation, noise at the  $\overline{WC}$  pin can be erroneously judged to be data, and this can cause writing to be forcibly interrupted.

3) Vcc noise

Noise and surges on the power supply line can cause malfunction. We recommend installing a bypass capacitor between the power supply and ground to eliminate this problem.

#### (3) Canceling modes

#### 1) Read commands

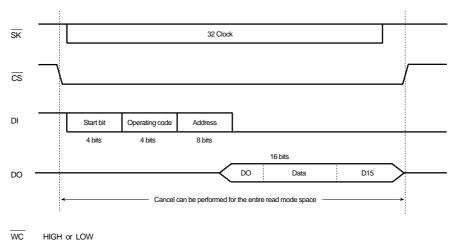
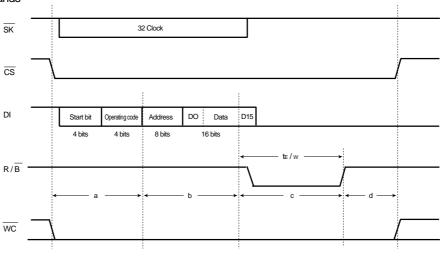


Fig.10

# Cancellation method: $\overline{\text{CS}}$ HIGH

#### 2) Write commands



# Canceling methods

- a: Canceled by setting CS HIGH. The WC pin is not involved.
- b: If the WC pin goes HIGH for even a second, writing is forcibly interrupted. Cancellation occurs even if the CS pin is HIGH. At this point, data has not been written to the memory, so the data in the designated address has not yet been changed.

Fig.11

- c: The operation is forcibly canceled by setting the WC pin to HIGH or turning off the power supply (although we do not recommend using this method). The data in the designated address is not guaranteed and should be written once again.
- d: If  $\overline{CS}$  is set to HIGH while the R /  $\overline{B}$  signal is HIGH (following the te/w timing), the IC is reset internally, and waits for the next command to be input.

# ●External dimension (Units : mm)

